

L11	133	(soi silicon-on-insulator silicon adj insulator thin adj film adj transistor\$2 tft).ti. and ((source and drain)adj (electrod\$2 wir\$4))and(((gate) adj(oxide dielectric insulat\$4))near5(remov\$4 etch\$4))and ((ldd low\$2 adj impurity mdd))	US-PGPUB; USPAT	OR	OFF	2005/12/06 14:33
L12	118	11 not 1	US-PGPUB; USPAT	OR	OFF	2005/12/06 14:35
L13	26	spacer\$2 and 12	US-PGPUB; USPAT	OR	OFF	2005/12/06 15:38
L14	26	"6307214"	US-PGPUB; USPAT	OR	OFF	2005/12/06 15:44
L15	119	"5518940" "5523257" "5563427"	US-PGPUB; USPAT	OR	OFF	2005/12/06 15:44
L16	29	15 and ((ldd low\$2 adj impurity mdd)) and spacer\$2	US-PGPUB; USPAT	OR	OFF	2005/12/06 15:45
L17	7393	257/72 257/59 257/347 438/149 438/479 438/517 438/48.ccls.	US-PGPUB; USPAT	OR	OFF	2005/12/06 16:15
L18	374	10 and 17	US-PGPUB; USPAT	OR	OFF	2005/12/06 16:15
L19	133	(soi silicon-on-insulator silicon adj insulator thin adj film adj transistor\$2 tft).ti. and ((source and drain)adj (electrod\$2 wir\$4))and(((gate) adj(oxide dielectric insulat\$4))near5(remov\$4 etch\$4))and ((ldd low\$2 adj impurity mdd))	US-PGPUB; USPAT	OR	OFF	2005/12/06 16:15
L20	140	(soi silicon-on-insulator silicon adj insulator thin adj film adj transistor\$2 tft)and ((source and drain)adj (electrod\$2 wir\$4))and(((gate) adj(oxide dielectric insulat\$4))near5(remov\$4 etch\$4))and ((ldd low\$2 adj impurity mdd)).clm.	US-PGPUB; USPAT	OR	OFF	2005/12/06 16:16
L21	101	20 not 19	US-PGPUB; USPAT	OR	OFF	2005/12/06 16:16
L22	41	17 and 21	US-PGPUB; USPAT	OR	OFF	2005/12/06 16:18
L23	0	"6549252" and spacer\$2	US-PGPUB; USPAT	OR	OFF	2005/12/06 16:18
L24	1	"6549252"	US-PGPUB; USPAT	OR	OFF	2005/12/06 16:19

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	70	(soi silicon-on-insulator silicon adj insulator thin adj film adj transistor\$2 tft)and ((source and drain)adj (electrod\$2 wir\$4))same(((gate) adj(oxide dielectric insulat\$4))near4(remov\$4 etch\$4))and ((ldd low\$2 adj impurity mdd))	US-PGPUB; USPAT	OR	OFF	2005/12/06 15:45
L2	1	"20050017239" and "505"	US-PGPUB; USPAT	OR	OFF	2005/12/06 13:50
L3	1	"20050017239" and (ldd spacer\$2)	US-PGPUB; USPAT	OR	OFF	2005/12/06 13:51
L4	1	"20050017239" and (offset)	US-PGPUB; USPAT	OR	OFF	2005/12/06 13:51
L5	1	"20050017239" and (offset)	US-PGPUB; DERWENT	OR	OFF	2005/12/06 13:51
L6	2	"20050017239"	US-PGPUB; DERWENT	OR	OFF	2005/12/06 13:52
L7	2	"2001254685"	US-PGPUB; JPO; DERWENT	OR	OFF	2005/12/06 13:53
L8	4	"2003069027"	US-PGPUB; JPO; DERWENT	OR	OFF	2005/12/06 13:53
L9	0	(soi silicon-on-insulator silicon adj insulator thin adj film adj transistor\$2 tft)and ((source and drain)adj (electrod\$2 wir\$4))and(((gate) adj(oxide dielectric insulat\$4))near5(remov\$4 etch\$4))and ((ldd low\$2 adj impurity mdd))	EPO; JPO; DERWENT	OR	OFF	2005/12/06 14:33
L10	1063	(soi silicon-on-insulator silicon adj insulator thin adj film adj transistor\$2 tft)and ((source and drain)adj (electrod\$2 wir\$4))and(((gate) adj(oxide dielectric insulat\$4))near5(remov\$4 etch\$4))and ((ldd low\$2 adj impurity mdd))	US-PGPUB; USPAT	OR	OFF	2005/12/06 16:16

L25	8	("5572047" "5610741" "5729308" "5763899" "6011275" "6072193" "6160271" "6307214").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/06 16:19
-----	---	--	------------------------------	----	-----	------------------